## **NPN Silicon Phototransistor**

### **OP599 Series**



#### Features:

- Dark blue injection-molded plastic package
- Variety of sensitivity ranges
- T-1¾ package style with TO-18 base
- Excellent optical lens surface
- Excellent chip placement



### **Description:**

Each device in this series consists of a NPN silicon phototransistor mounted in a dark blue plastic injection molded shell package, with a narrow receiving angle that provides excellent on-axis coupling and optical/mechanical axis alignment. The shell also provides excellent optical lens surface, control of chip placement and consistency of the outside package dimensions.

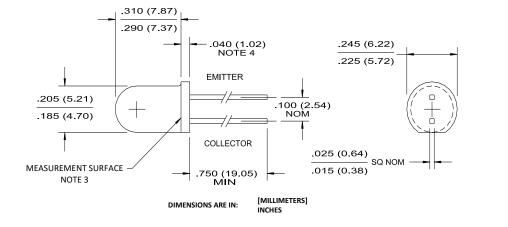
The **OP599** series sensors are 100% production tested for close correlation with OPTEK GaAIAs emitters.

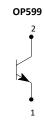
Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

### **Applications:**

- Applications requiring a narrow receiving angle
- · Applications that are space-limited

Ordering Information									
Part Number	Sensor	Viewing Angle	Lead Length						
OP599A			0.75"						
OP599B (Obsolete)	Transistor	20°							
OP599C									







Pin #	Sensor		
1	Emitter		
2	Collector		

#### **CONTAINS POLYSULFONE**

To avoid stress cracking, we suggest using ND Industries' **Vibra-Tite** for thread-locking. **Vibra-Tite** evaporates fast without causing structural failure in OPTEK'S molded plastics.

General Note

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## **Electrical Specifications**

### **Absolute Maximum Ratings** (T<sub>A</sub> = 25° C unless otherwise noted)

Storage and Operating Temperature Range	-40° C to +100° C
Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5 V
Continuous Collector Current	50 mA
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C <sup>(1)</sup>
Power Dissipation	100 mW <sup>(2)</sup>

### Electrical Characteristics (T<sub>A</sub> = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
I <sub>C(ON)</sub>	On-State Collector Current OP599A OP599C	2.35 0.40	1 1	- 1.95	mA	See Note 3.
I <sub>CEO</sub>	Collector-Dark Current	-	-	100	nA	V <sub>CE</sub> = 10.0 V, E <sub>E</sub> = 0
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	30	-	-	V	Ι <sub>C</sub> = 100 μΑ
V <sub>(BR)ECO</sub>	Emitter-Collector Breakdown Voltage	5.0	1	1	٧	Ι <sub>Ε</sub> = 100 μΑ
V <sub>CE(SAT)</sub>	Collector-Emitter Saturation Voltage	-	-	0.40	V	$I_C = 100 \mu A, E_E = 0.25 \text{ mW/cm}^{2 (3)}$

#### Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering. A maximum 20 grams force may be applied to the leads when soldering.
- 2. Derate linearly 1.33 mW/° C above 25° C.
- 3.  $V_{CE} = 5 \text{ V}$ . Light source is an unfiltered GaAlAs emitting diode operating at peak emission wavelength of 890 nm and  $E_{E(APT)}$  of 0.25 mW/cm<sup>2</sup>.
- 4. This dimension is held to within ±0.005" on the flange edge and may vary up to ±0.020" in the area of the leads.

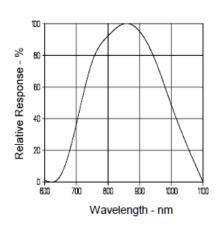
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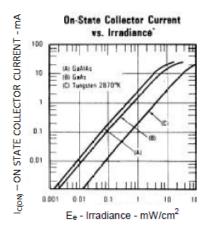
## **OP599 Series**



### **Performance**

Typical Spectral Response





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TT Electronics:

OP599A OP599C